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| SPEC SHEET (FOR REFERENCE) | SHEET No. | Rev. | Page. |
| | G05013A | 1 | 1 of 1 |

TYPE:6PT806N2T4U

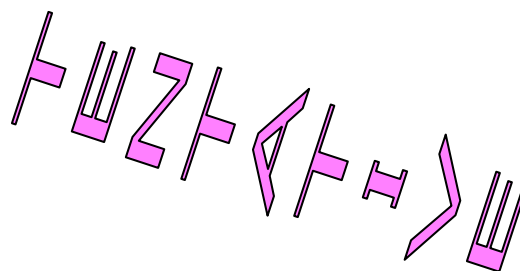
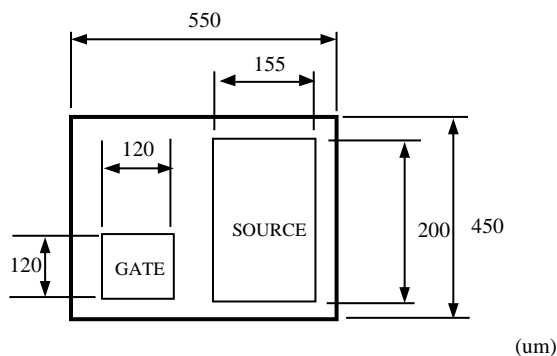
| | |
|------------------------|---------------|
| CHIP SIZE | 0.55 * 0.45mm |
| WAFER SIZE | 6inch |
| POSSIBLE DIE PER WAFER | 62,476pcs |

Maximum Ratings (Ta=25°C)

| Characteristics | Symbol | Ratings | Unit |
|----------------------|--------|---------|------|
| Drain-source voltage | VDSS | 50 | V |
| Gate-source voltage | VGSS | ±20 | V |

WAFER PROBING SPEC (Ta=25C)

| No | MODE | LIMIT | | | | CONDITIONS |
|----|----------|-------|-----|------|------|------------------|
| | | MIN. | Typ | MAX. | UNIT | |
| 1 | IGSS | | | ±8 | nA | VGS=±20V VDS=0V |
| 2 | IDSS | | | 50.0 | nA | VDS=50V VGS=0V |
| 3 | BVDSS | 55 | | | V | ID=10μA |
| 4 | VTH | 1.0 | | 1.4 | V | ID=250μA |
| 5 | RDS(on)1 | | 1.5 | 2.1 | Ω | ID=50mA VGS=5.0V |
| 6 | RDS(on)2 | | 1.2 | 1.8 | Ω | ID=500mA VGS=10V |
| 7 | VSD | 0.5 | | 1.4 | V | I=115mA VGS=0V |
| 8 | Yfs | 200 | | | mS | Vds=10V Id=200mA |



NOTE: